

688396.SH

IDM

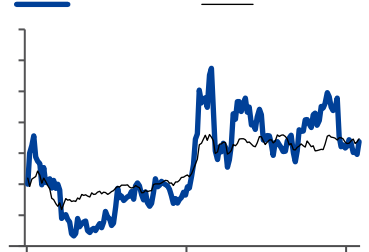
5G

MOSFET

12

8

12



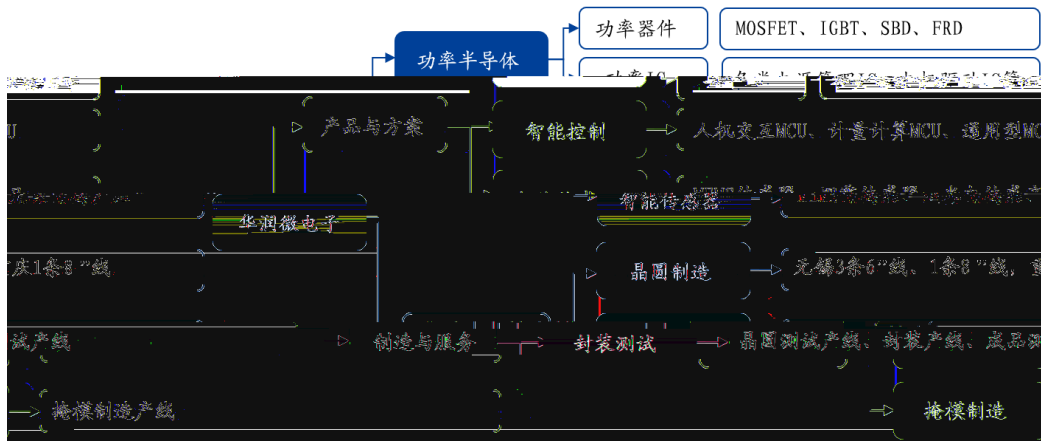
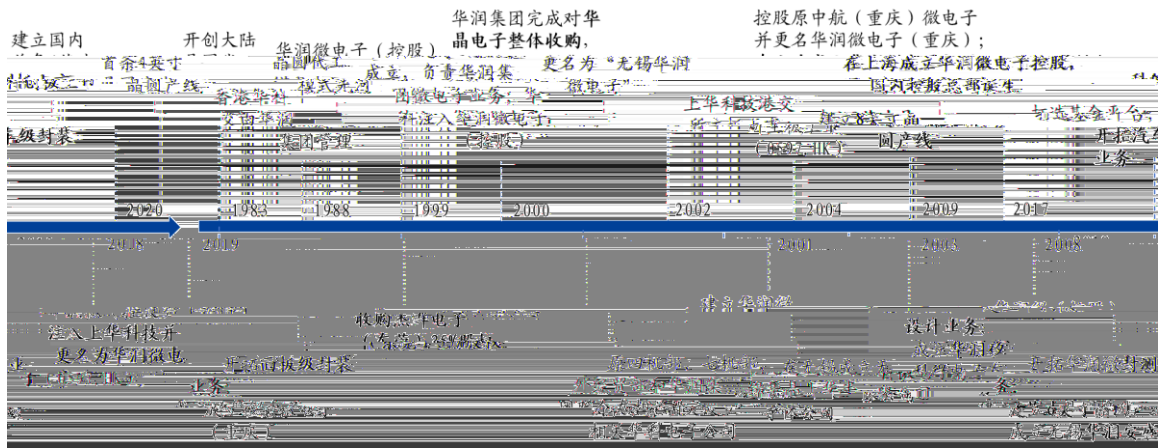
2018A 2019A 2020E 2021E 2022E





IDM

1.1



| 2019 | MOS |
|-------------|------------|
|-------------|------------|

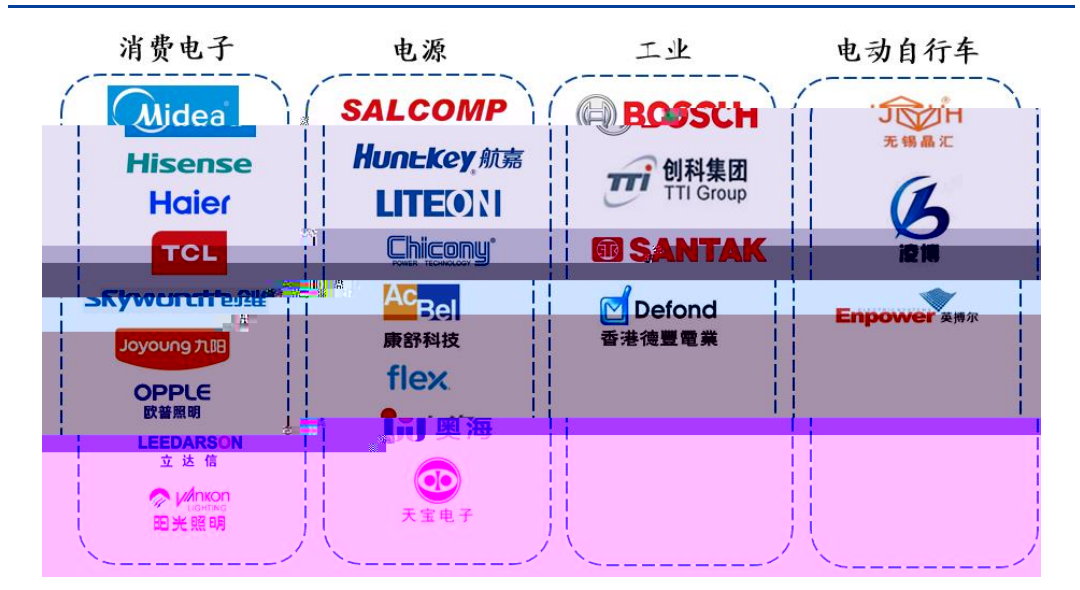
| |
|-----------|
| 16 |
|-----------|

| |
|-------------|
| 7.5% |
|-------------|

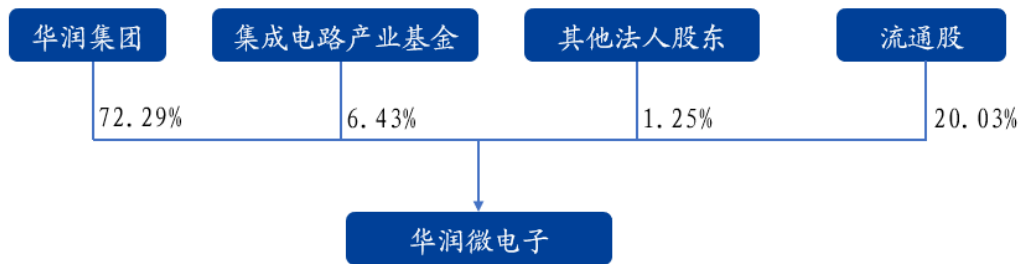
IC

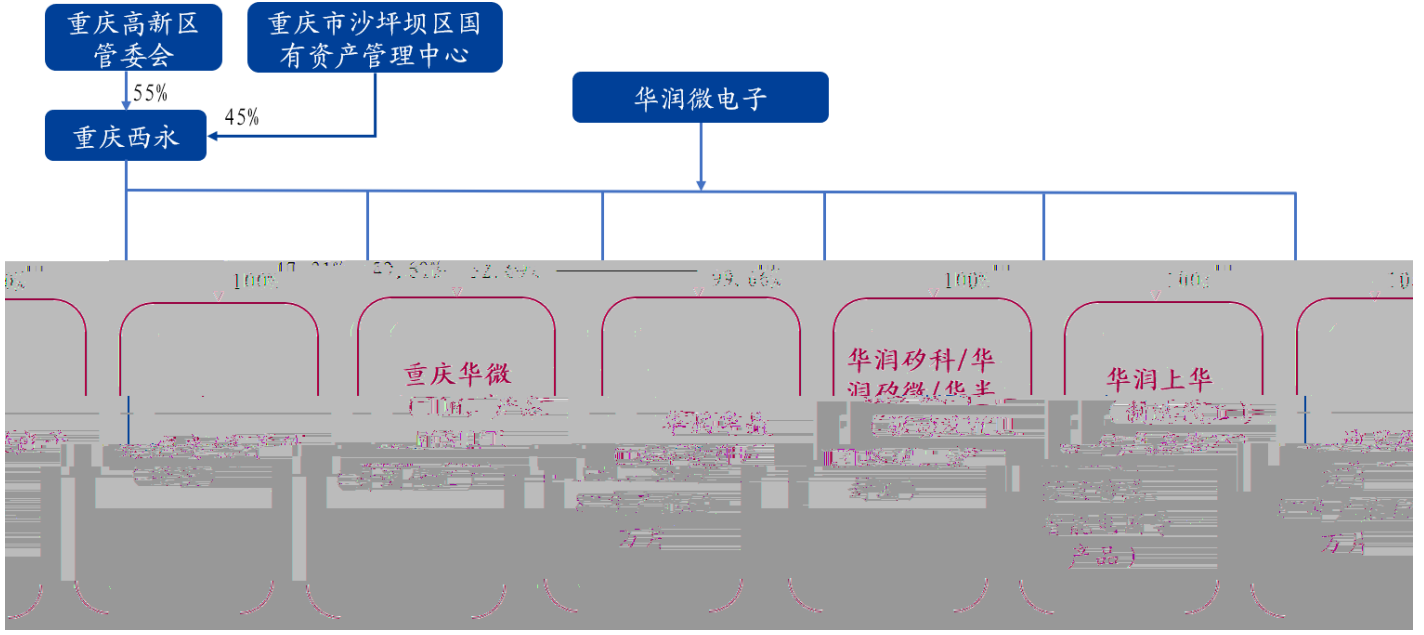
2018

| |
|--|
| |
| |
| |
| |
| |

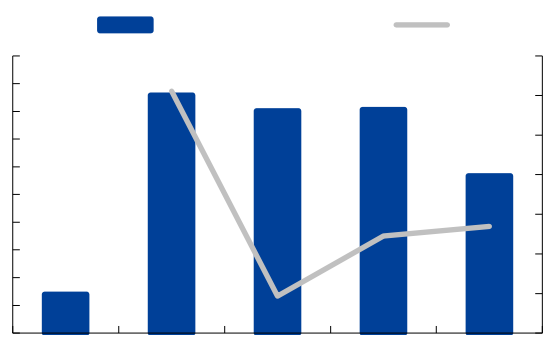
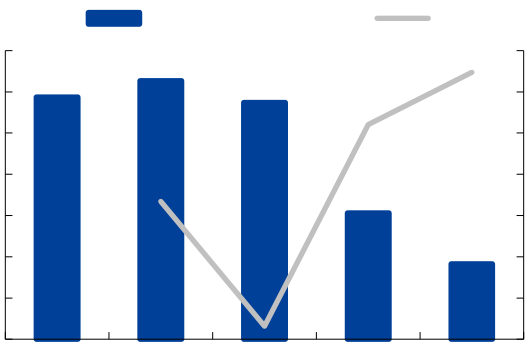


1.3

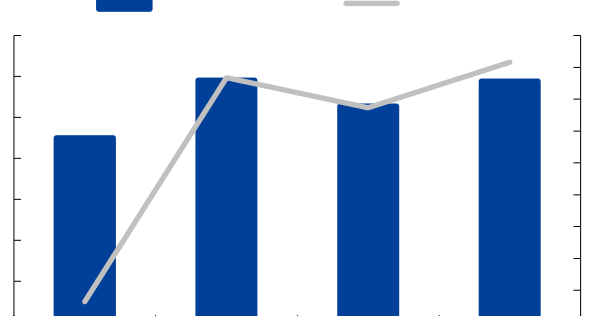
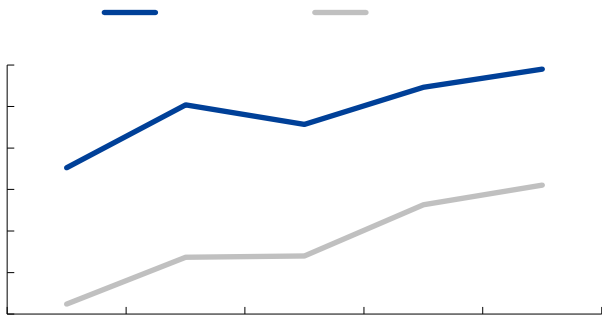


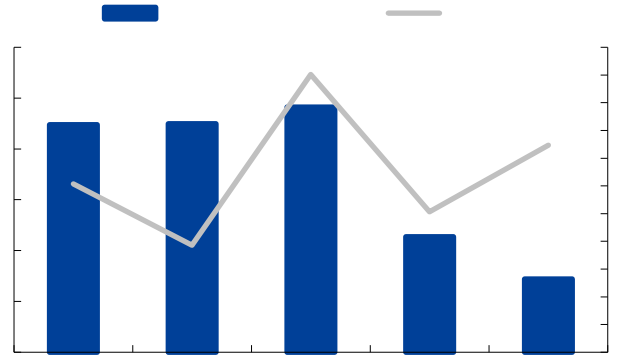
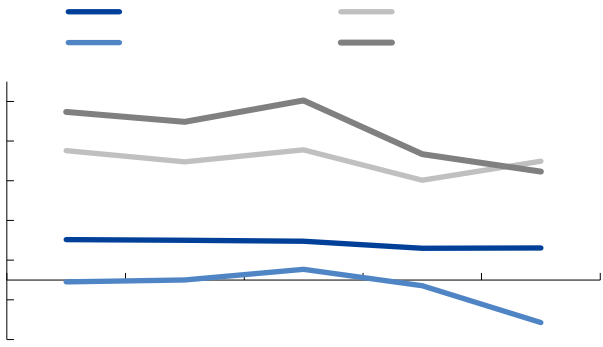


1.4



| 2019 | 2018 | 2017 | 2019 | 2018 | 2017 | 2019 | 2018 | 2017 |
|------|------|------|--------|--------|--------|-------|-------|-------|
| 25.2 | 26.8 | 23.4 | 44.1% | 42.9% | 39.9% | 29.5% | 34.0% | 19.6% |
| | | | | | | | | |
| | | | | | | | | |
| 31.8 | 35.7 | 35.2 | 55.9% | 57.1% | 60.1% | 17.8% | 18.6% | 16.3% |
| | | | | | | | | |
| 57.0 | 62.6 | 58.6 | 100.0% | 100.0% | 100.0% | 22.9% | 25.2% | 17.6% |

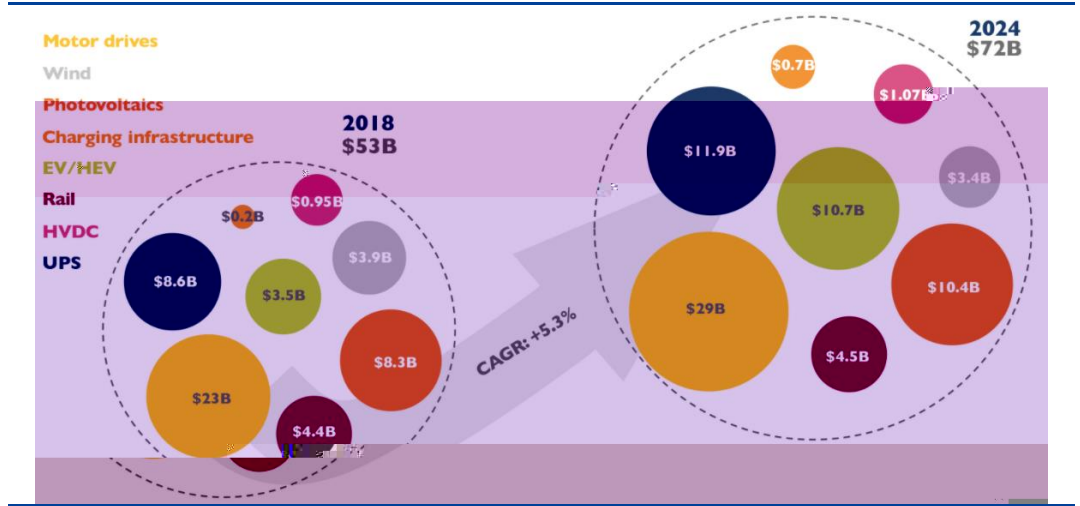




Yole 2018

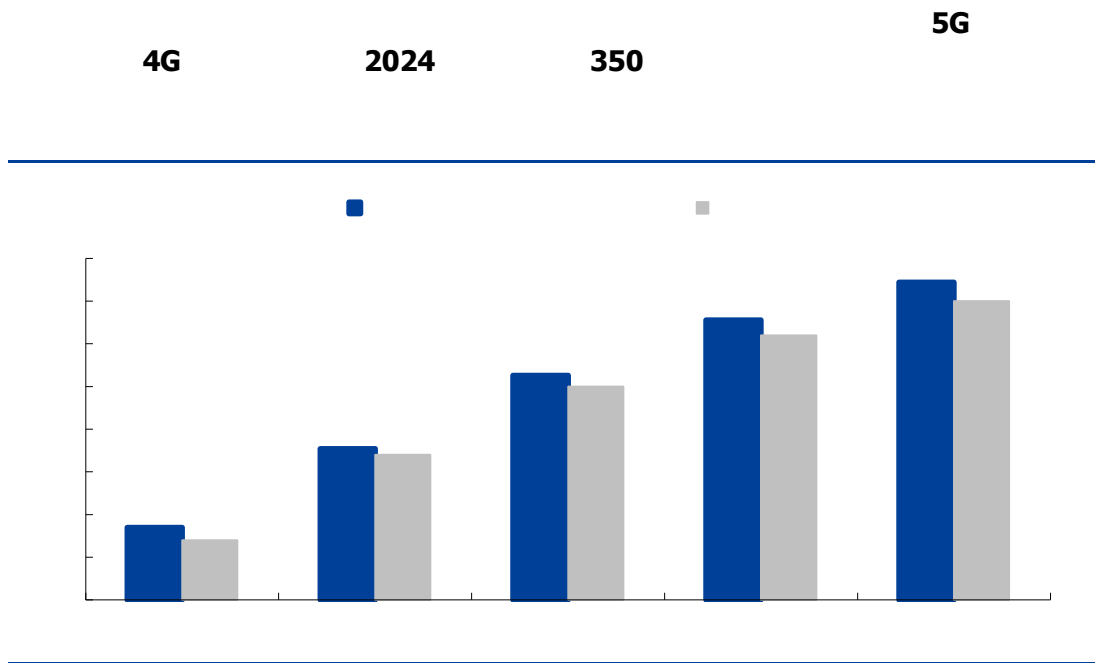
2.1 5G

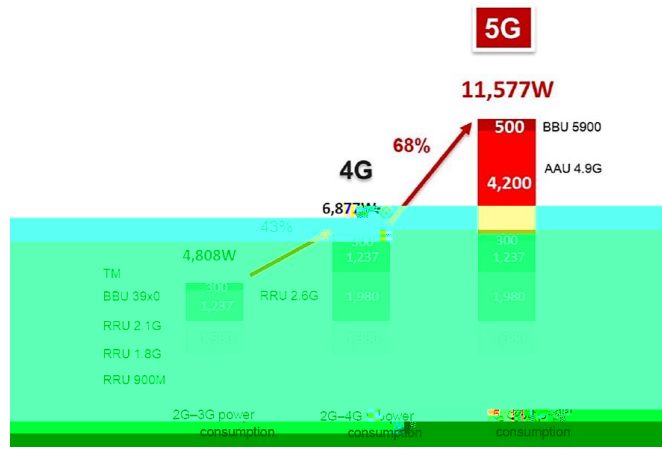




2.1.2 5G

| 5G | | 5G | | |
|--------|--------|--------|-------|-------|
| 2.3GHz | 3.5GHz | 4.9GHz | 26GHz | 29GHz |
| | | | | |



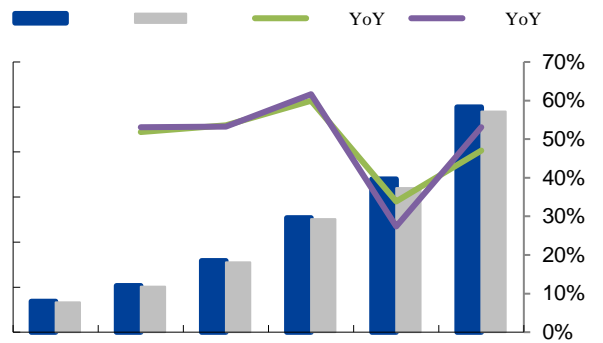
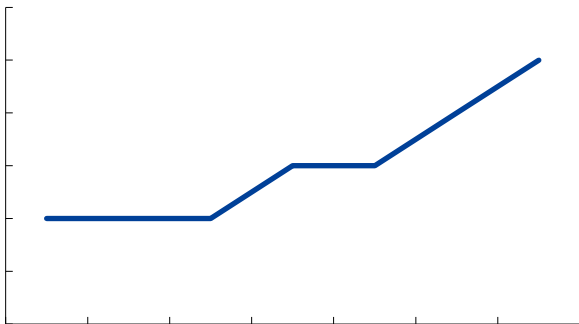


2.2

IBGT

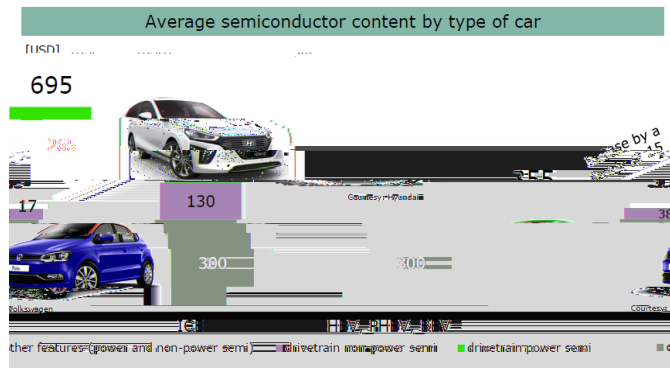
MOS

| | | | |
|------|------|-----------|------|
| 2011 | 8000 | 2017 | 79.4 |
| 2.7% | | 2012-2020 | 2020 |
| 500 | 200 | | |

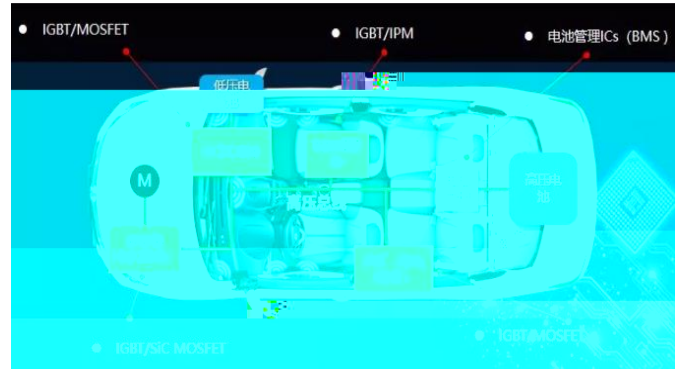


355 /
695
17 /
265 15

34



35

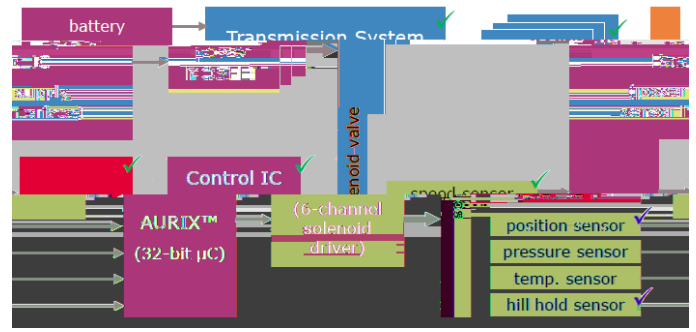
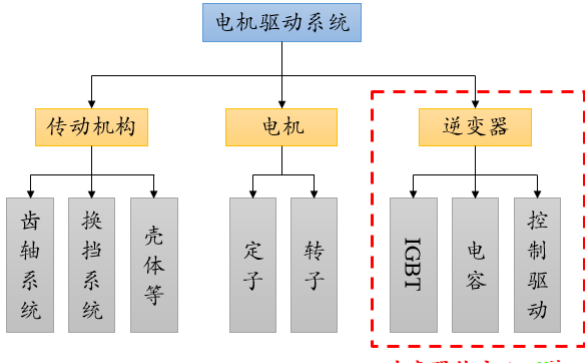


36

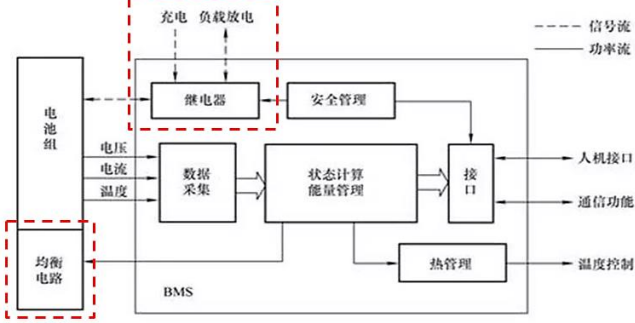
| | SSV | Mild HEV | Full HEV | PHEV with EREV | EV BEV/FCV |
|-------|--------------------------|----------------------------|--------------------------|--------------------|------------------------------|
| / | MOSFET 1.5-10kw 3.5kw | | | | |
| DC/DC | | | MOSFET 1.5-3kw 2.25kw | | |
| | | MOSFET/IGBT 5-20kw 15kw | | IGBT 20-150kw 70kw | |
| OBC + | | | | IGBT 20-40kw 30kw | MOSFET 3-6kw IGBT 10-40kw |
| | 3.5kw | 17.25kw | 52.25kw | 56.75-102.5kw | |

NE

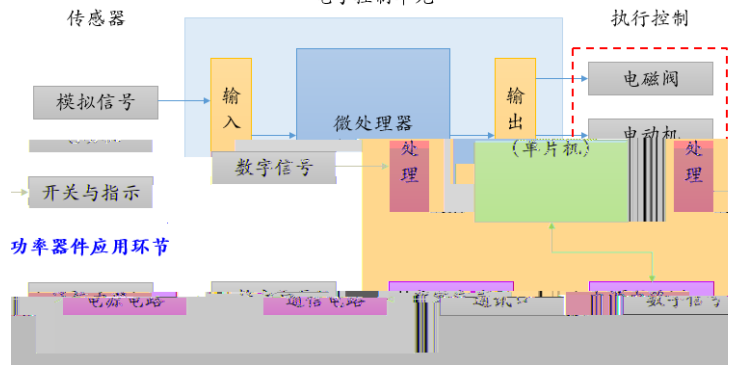
IGBT
SiC MOSFET



功率器件应用环节

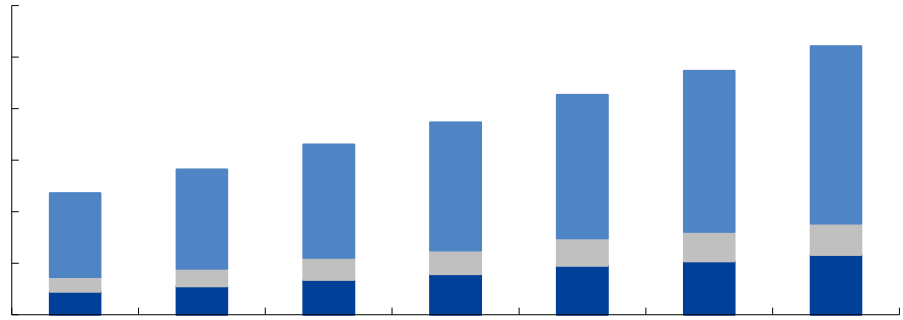


电子控制单元



EV/HEV

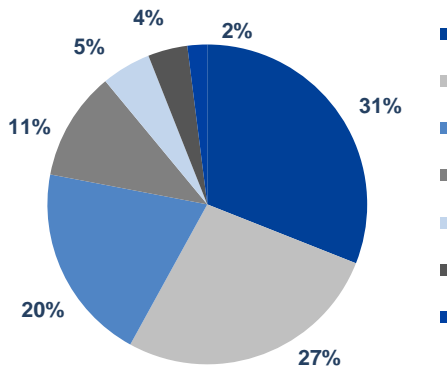
| Yole | | 2017 | | BEV | | EV/HEV | | 2.2 | | 2023 | |
|------|------|------|--|-----|-----|--------|--|-----|------|-------|--|
| | | | | | 22% | 5.8 | | | | | |
| | 2017 | 8.1 | | | | 17.2 | | | | | |
| | | | | | | | | | CAGR | 43.4% | |
| | | | | | | | | | | HEV | |



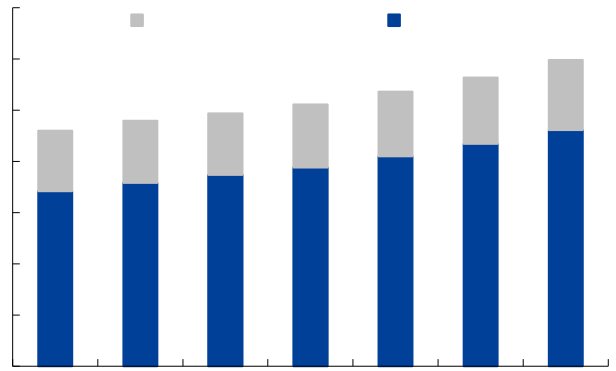
IGBT

IGBT
 31% HIS Markit 2018 IGBT
 IGBT 2017 50 IGBT 2020-2025 47.9 Yole 2019
 CAGR 5%

2018 IGBT



IGBT



Yole

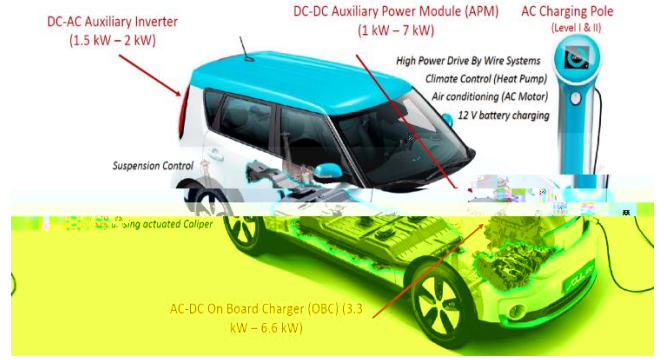
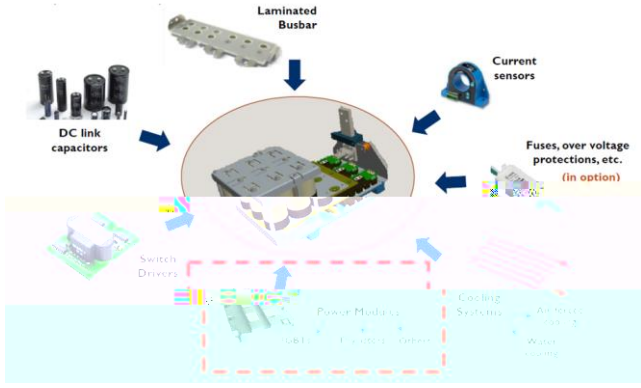
IGBT

50%

IGBT IGBT

IGBT

IGBT
/ (DC/AC)



IGBT

IGBT

36

96

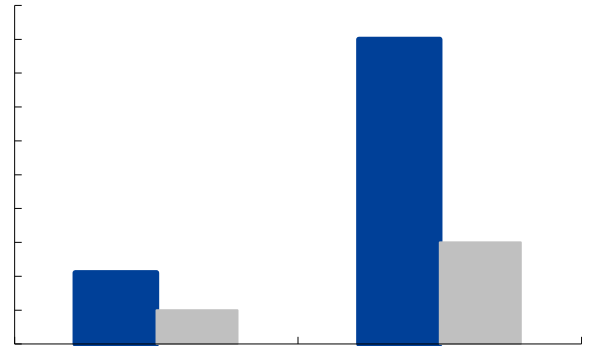
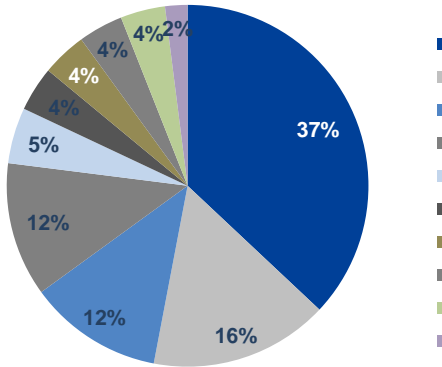
15~20%

40%

IGBT
Model X
650

20%
132 IGBT

5%



Trendforce

IGBT
2018-2025 8
IGBT

IGBT
2025 900
100 8

Trendforce
IGBT 210
2025 300

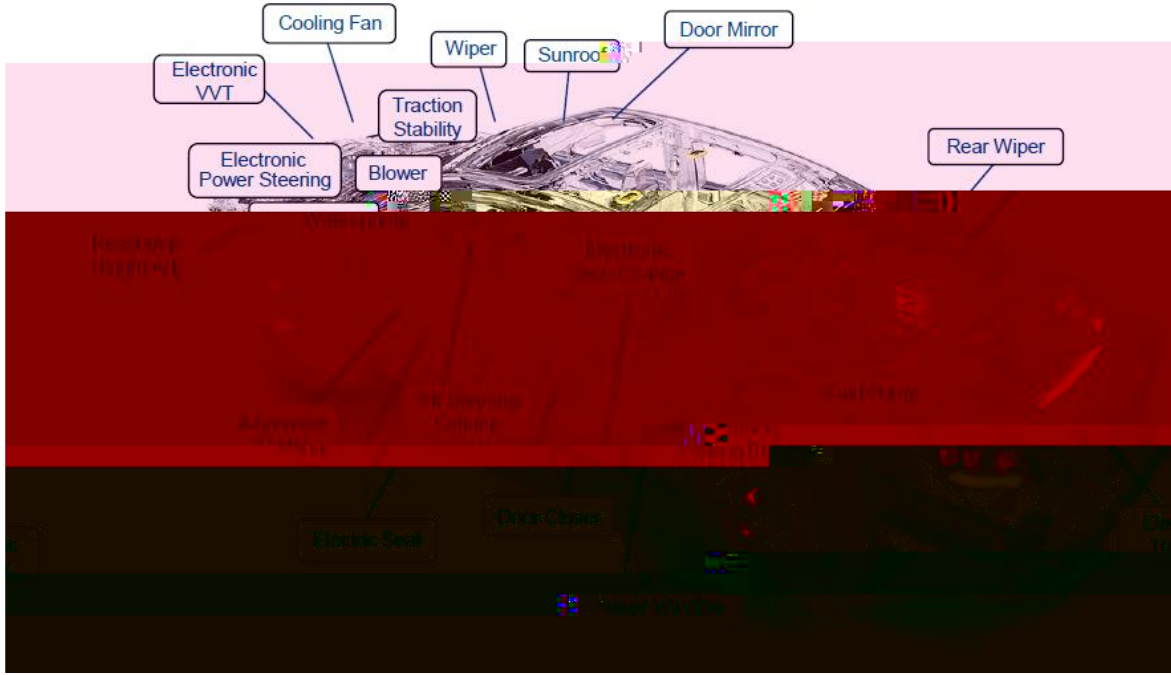
MOSFET

IGBT MOSFET

IGBT
MOSFET

MOSFET

IGBT 1000V 350A

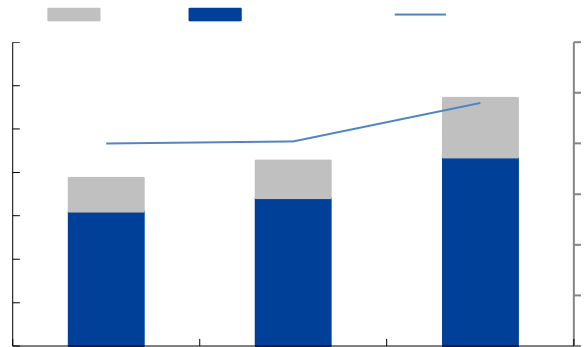
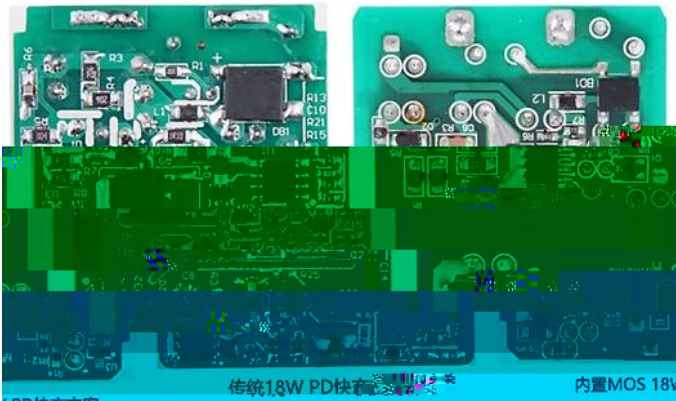


Didodes

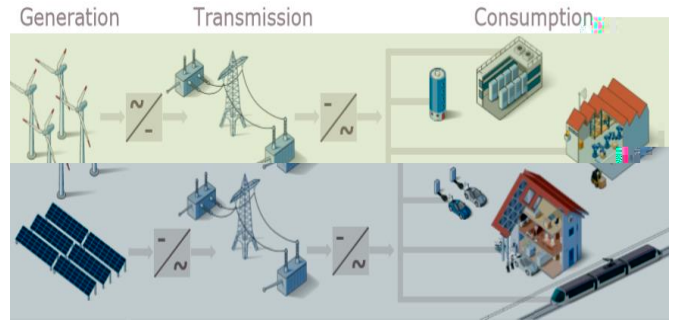
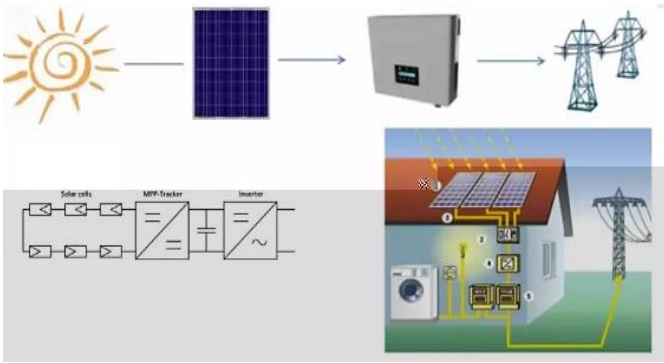
2.3

MOSFET

| | | | | |
|-----|--------------|------|-----------|-------|
| | | | iPhone 12 | |
| 20% | BCC Research | 2017 | | 85.49 |
| | | 2022 | 27.4 | 24% |
| | MOSFET | MOS | | |
| | MOS | | MOS | |



15%-30%



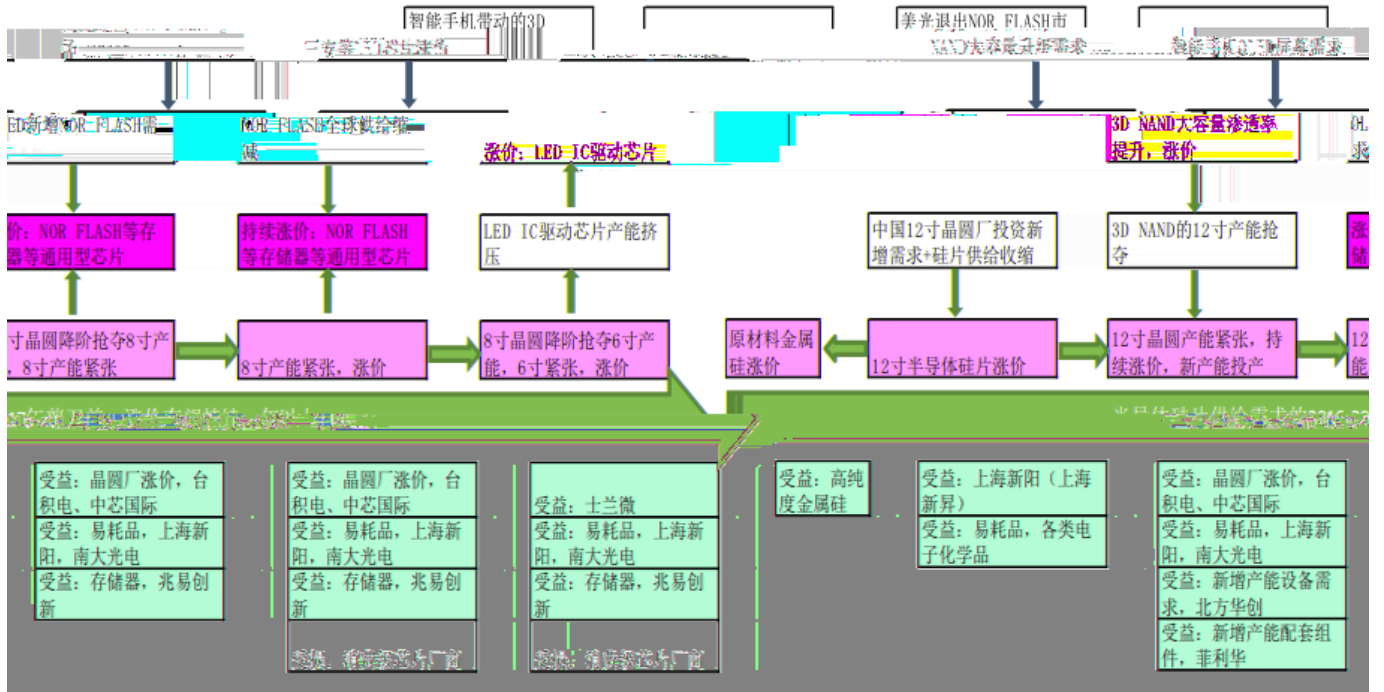
BP 2018 Energy Outlook

IGBT

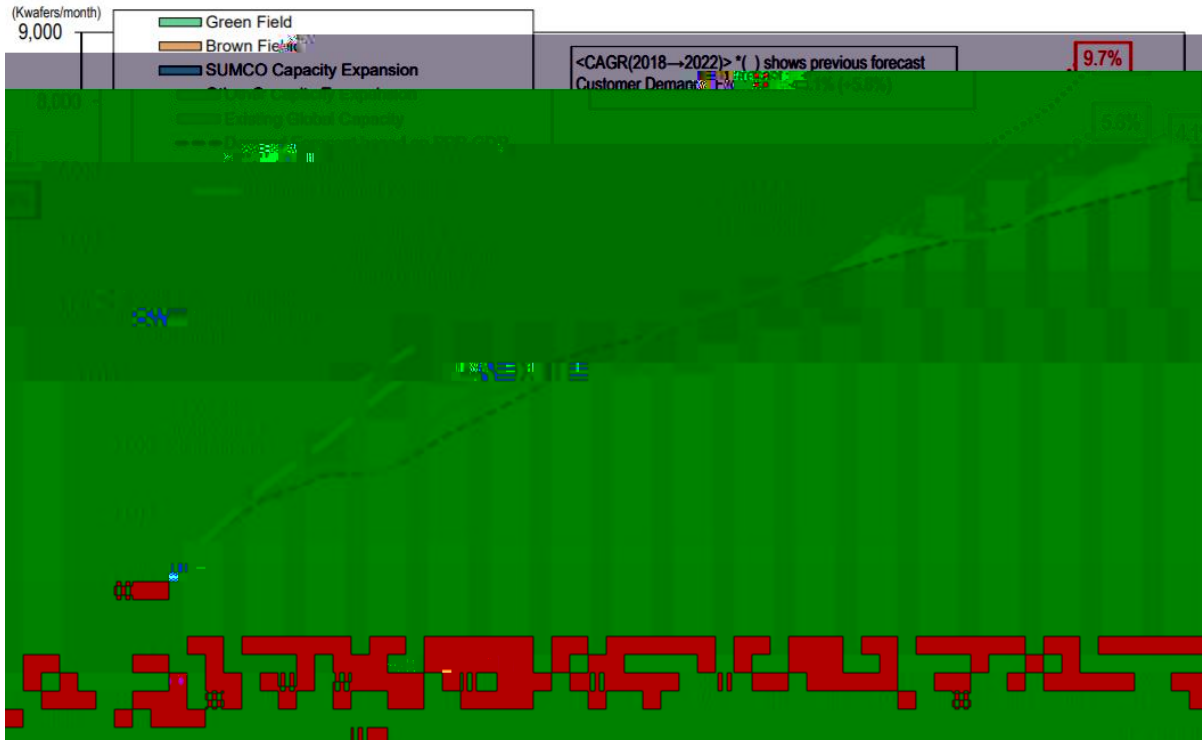
| | | | | | | | |
|------|----|------|----|------|----|------|------|
| | | | | CRH3 | | 4 | |
| | 32 | IGBT | | IGBT | | 128 | IGBT |
| | | | 10 | | | | 3300 |
| IGBT | | | | 10 | 20 | 3300 | IGBT |
| | | | | 15 | | | |

3.1

| | | | | | | |
|--|----|-----|--|-----|--|-----------|
| | / | | | 4-6 | | |
| | | | | | | raw wafer |
| | | 10% | | | | |
| | 12 | | | 8 | | |



| | | | | | | | | |
|----------|-----|------|------|-----|------|------|-------|------|
| | 12 | | 2020 | | | | | |
| | | 12 | 2001 | | | | SUMCO | 2019 |
| | 12 | 602 | / | 12 | | | | DRAM |
| EXCHANGE | 190 | 2019 | DRAM | 120 | / | NAND | | |
| | / | | 12 | | 2023 | 200 | / | |



SUMCO

8

8

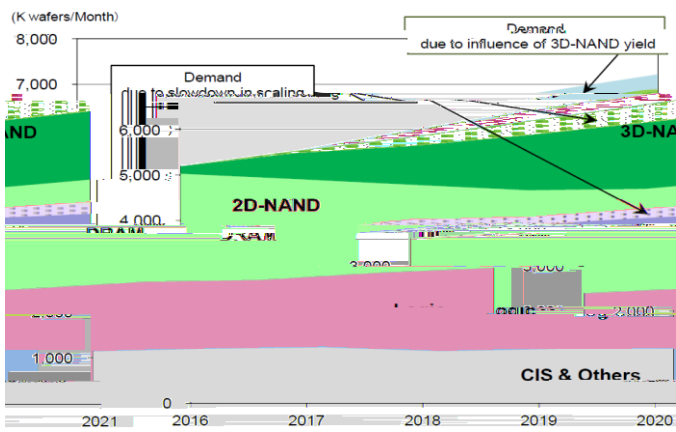
CIS PMIC Nor Flash

IC MEMS

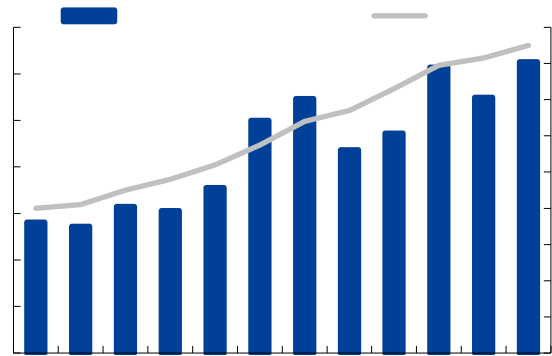
59 12

60 12

2020-2023



Semico



AnySilicon

8

6

12

8

MEMS

1990 2007

8

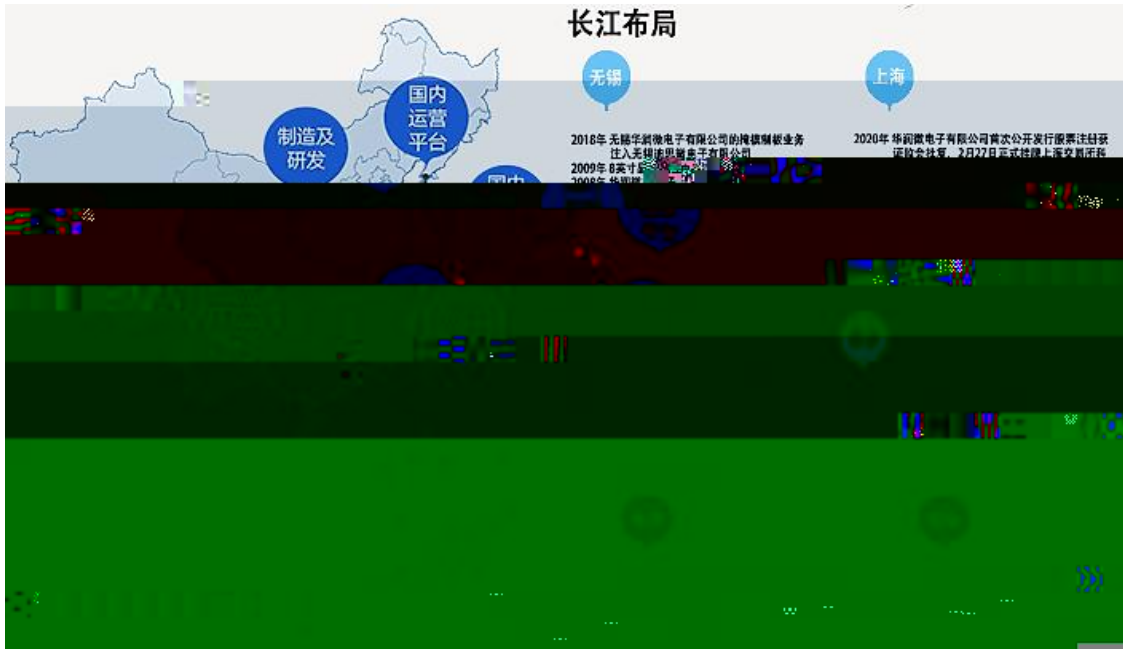
12

IC Insights

12

2009-2017

4.2



12

8

PE-TTM

PB

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| | |

